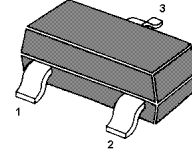
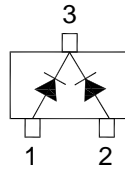


SB705D

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for general purpose detection and high speed switching applications



Marking Code: **RB**
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

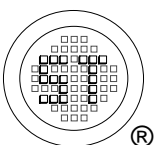
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	40	V
Mean Rectifying Current	I_O	30	mA
Peak Forward Surge Current ¹⁾	I_{FSM}	200	mA
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 125	$^\circ\text{C}$

¹⁾ 60 Hz for 1 ∞

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$	V_F	-	0.37	V
Reverse Current at $V_R = 10\text{ V}$	I_R	-	1	μA
Capacitance between Terminals at $V_R = 1\text{ V}$, $f = 1\text{ MHz}$	C_T	2	-	pF

Note: ESD sensitive product handling required.



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Dated : 09/08/2006

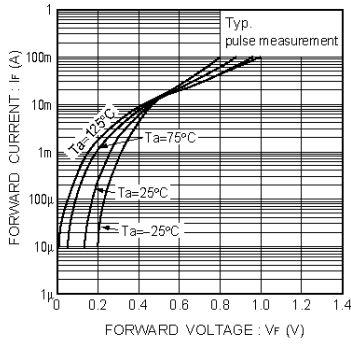


Fig. 1 Forward characteristics

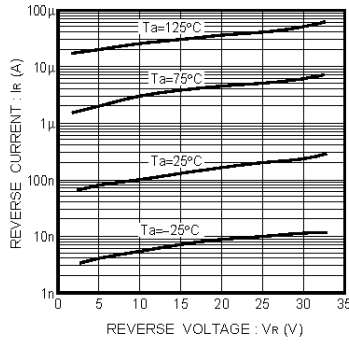


Fig. 2 Reverse characteristics

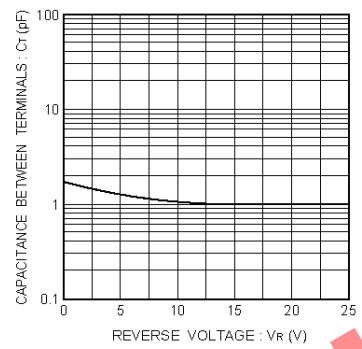


Fig. 3 Capacitance between terminals characteristics

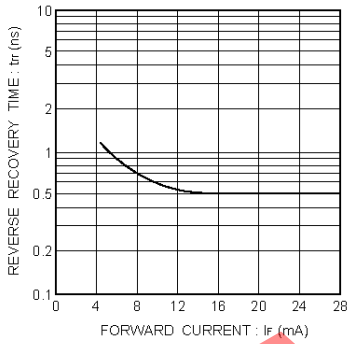


Fig. 4 Reverse recovery time characteristics

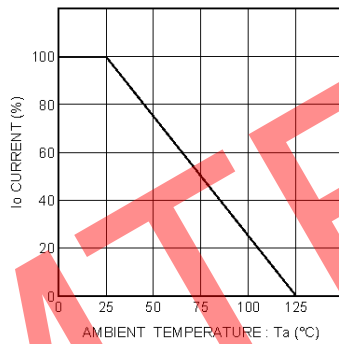
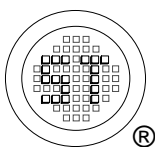


Fig. 5 Derating curve (mounting on glass epoxy PCBs)



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